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Application Number	
Filing Date	11/26/2003
First Named Inventor	TADAHIRO OHMI
Art Unit	2818
Examiner Name	David Vu
Attorney Docket Number	040258-0306939

(Use as many sheets as necessary)

Sheet	1	of	1
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U. S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
PV	A	JP 5-267684	10-15-1993	OZAWA		
	B	JP 59-105371	06-18-1984	KOMORI		
	C	JP 8-51164	02-20-1996	MORITA		
	D	JP 9-205155	08-05-1997	TAKABAYASHI		
PV	E	JP 9-213820	08-15-1997	USHIYAMA et al.		

Examiner Signature	<i>Shuland</i>	Date Considered	06/17/04
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known			
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		First Named Inventor	TADAHIRO OHMI		
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Sheet	1	of	1	Attorney Docket Number	040258-0306939

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DV	A	ITO ET AL., "Silicon Oxynitridation With Inductively Coupled Oxygen-Nitrogen Mixed Plasma," Japan J. Appl. Phys., p. 612-616, (1997).	
DV	B	HIRAYAMA ET AL., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma," IEDM, p. 249-252, (1999).	
DV	C	SAITO ET AL., "Low Temperature Formation of Gate-Grade Silicon Nitride Film Employing Microwave-Excitation High-Density Plasma," Technical Report of IEICE, p. 85-90, (1999).	

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